# imall

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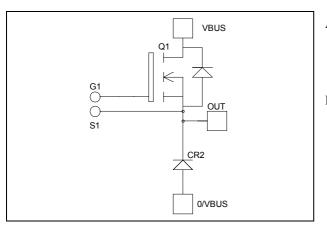
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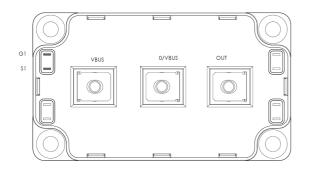




### APTM20SKM04G

### Buck chopper MOSFET Power Module





### $V_{DSS} = 200V$ $R_{DSon} = 4m\Omega \text{ typ } @ \text{ Tj} = 25^{\circ}C$ $I_{D} = 372A @ \text{ Tc} = 25^{\circ}C$

#### Application

- AC and DC motor control
- Switched Mode Power Supplies

#### Features

- Power MOS 7<sup>®</sup> MOSFETs
  - Low R<sub>DSon</sub>
    - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
- Very rugged
- Kelvin source for easy drive
  - Very low stray inductance
    - Symmetrical design
    - M5 power connectors
  - High level of integration

#### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

#### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V <sub>DSS</sub>	Drain - Source Breakdown Voltage	200	V	
т	Continuous Drain Current	$T_c = 25^{\circ}C$	372	
I <sub>D</sub>		$T_c = 80^{\circ}C$	278	А
I <sub>DM</sub>	Pulsed Drain current	1488		
V <sub>GS</sub>	Gate - Source Voltage	±30	V	
R <sub>DSon</sub>	Drain - Source ON Resistance		5	mΩ
P <sub>D</sub>	Maximum Power Dissipation	$T_c = 25^{\circ}C$	1250	W
I <sub>AR</sub>	Avalanche current (repetitive and non repetitive)		100	А
E <sub>AR</sub>	Repetitive Avalanche Energy		50	mJ
E <sub>AS</sub>	Single Pulse Avalanche Energy		3000	1113

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



#### All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

#### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 200V$ 7	$\Gamma_j = 25^{\circ}C$			500	μA
		$V_{GS} = 0V, V_{DS} = 160V$ T	$\Gamma_j = 125^{\circ}C$			2000	
R <sub>DS(on)</sub>	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 186A$			4	5	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 10 \text{mA}$		3		5	V
I <sub>GSS</sub>	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$				±200	nA

#### **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C <sub>iss</sub>	Input Capacitance	$V_{GS} = 0V$		28.9		
Coss	Output Capacitance	$V_{\rm DS} = 25 V$		9.32		nF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1MHz		0.58		
Qg	Total gate Charge	$V_{GS} = 10V$		560		nC
$Q_{gs}$	Gate – Source Charge	$V_{Bus} = 100V$		212		
$Q_{gd}$	Gate – Drain Charge	$I_{\rm D} = 372 \rm A$		268		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive switching @ 125°C		32		ns
T <sub>r</sub>	Rise Time	$V_{GS} = 15V$ $V_{Bus} = 133V$ $I_D = 372A$ $R_G = 1.2\Omega$		64		
T <sub>d(off)</sub>	Turn-off Delay Time			88		
$T_{\rm f}$	Fall Time			116		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V$ , $V_{Bus} = 133V$ $I_D = 372A$ , $R_G = 1.2\Omega$		3396		T
$E_{\text{off}}$	Turn-off Switching Energy			3716		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V$ , $V_{Bus} = 133V$ $I_D = 372A$ , $R_G = 1.2\Omega$		3744		т
E <sub>off</sub>	Turn-off Switching Energy			3944		μJ

#### Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			200			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =200V	$T_j = 25^{\circ}C$			250	μA
1 KM			$T_{j} = 125^{\circ}C$			750	μ
I <sub>F</sub>	DC Forward Current		$T_c = 80^{\circ}C$		300		Α
	Diode Forward Voltage	$I_{\rm F} = 300 {\rm A}$		1 1.1		1.1	
V <sub>F</sub>		$I_{\rm F} = 600 {\rm A}$			1.4		V
		$I_{\rm F} = 300 {\rm A}$	$T_{j} = 125^{\circ}C$		0.9		
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25^{\circ}C$		60		ns
۲r	Reverse Recovery Time	$I_{\rm F} = 300 {\rm A}$ $V_{\rm R} = 133 {\rm V}$	$T_j = 125^{\circ}C$		110		115
Qrr	Reverse Recovery Charge	$di/dt = 600 A/\mu s$	$T_j = 25^{\circ}C$		600		nC
Zu			$T_{j} = 125^{\circ}C$		2520		ne

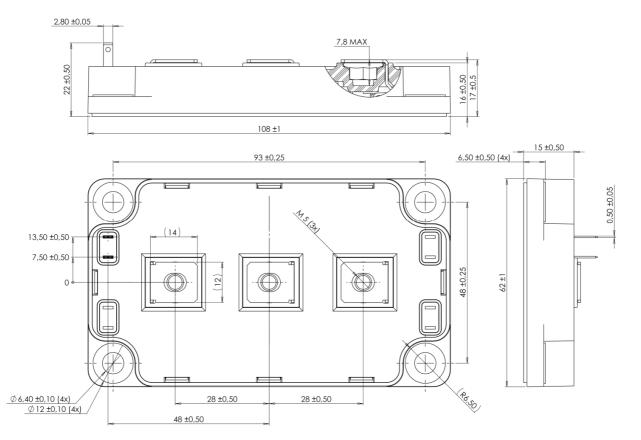


### APTM20SKM04G

#### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance Transistor Diode		Transistor			0.1	°C/W
<b>R</b> <sub>th</sub> JC			Diode			0.2	C/ W
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range			-40		150	
T <sub>STG</sub>	Storage Temperature Range			-40		125	°C
T <sub>C</sub>	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Torque		For terminals	M5	2		3.5	19.111
Wt	Package Weight					300	g

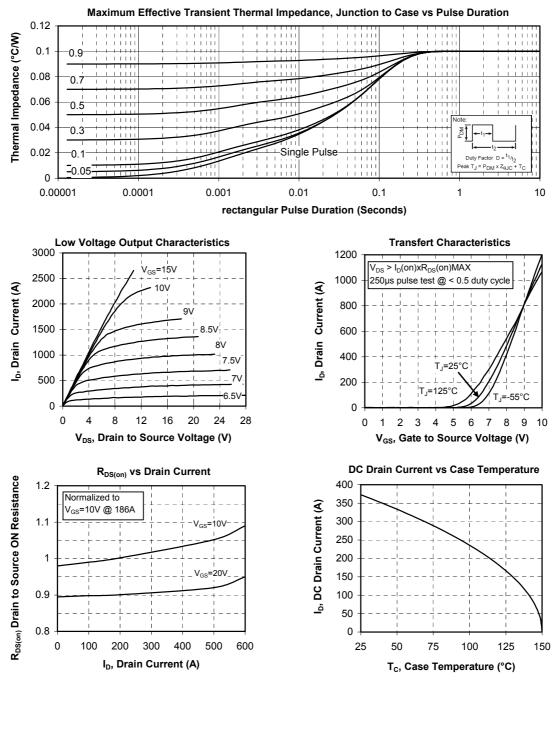
#### SP6 Package outline (dimensions in mm)



See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

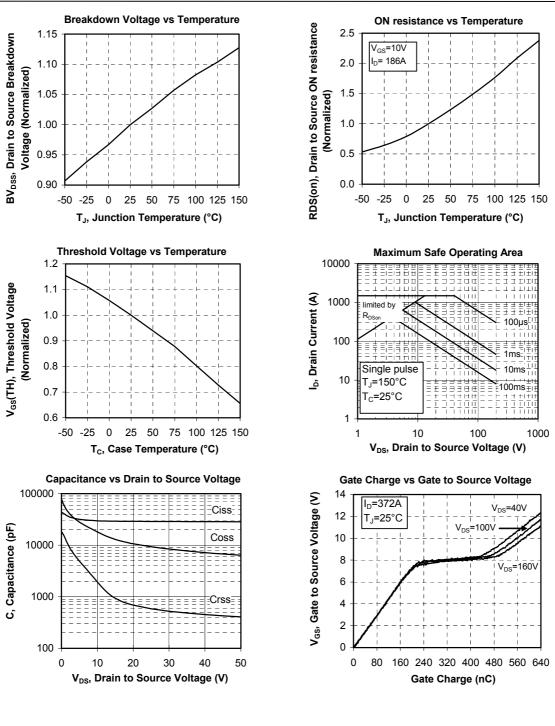


#### **Typical Performance Curve**





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APTM20SKM04G-Rev 3 October, 2012

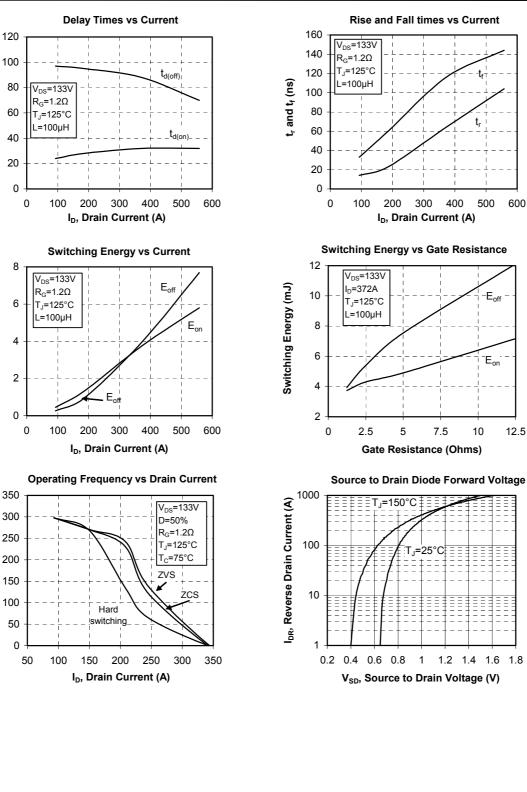


t<sub>d(on)</sub> and t<sub>d(off)</sub> (ns)

Eon and Eoff (mJ)

Frequency (kHz)

### APTM20SKM04G





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